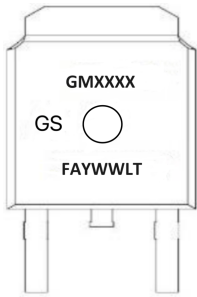
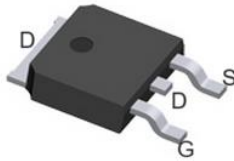


Product Summary

V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
30	4.3 @ $V_{GS} = 10V$	80 ⁽¹⁾

View and Internal Schematic Diagram



TO-252

NOTE:
 LOGO - GS
 GMXXXXX- Part number code
 F - Fab location code
 A - Assembly location code
 Y - Year code
 WW - Week code
 L&T - Assembly lot code

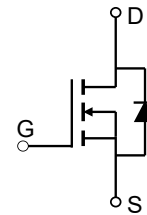
Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Application

- Synchronous rectification
- PWM Application
- Load switching
- Power Management

Equivalent circuit



Absolute maximum rating@25°C

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	46	A
I_{DM}	Pulsed Drain Current ²	320	A
EAS	Single Pulse Avalanche Energy ³	282	mJ
I_{AS}	Avalanche Current	75	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	70	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristic

Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	1.8	°C/W
Thermal resistance, junction-to-ambient ⁽⁴⁾	Steady state	$R_{\theta JA}$	50	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0, I _D = 250 μA	30			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0	1.5	2.0	V
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		3.8	4.3	mΩ
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 30 A		6.4	7.2	mΩ
Gate Resistance	R _g	f=1MHZ		3.1		Ω
Dynamic ⁽⁵⁾						
Total gate charge V _{GS} = 10V	Q _g	V _{DS} = 15 V, I _D = 30 A, V _{GS} = 10 V		39.2		nC
Gate-source charge	Q _{gs}			6		
Gate-drain charge	Q _{gd}			8.2		
Turn-on delay time	t _{d(on)}	V _{DS} = 15 V, I _D = 30 A, V _{GS} = 10 V, R _{GEN} = 2.9 Ω		22		ns
Rise time	t _r			26		
Turn-off delay time	t _{d(off)}			44		
Fall time	t _f			14		
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1950		pF
Output capacitance	C _{oss}			220		
Reverse transfer capacitance	C _{rss}			165		
Diode Characteristics						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,6}	I _S	V _G =V _S =0V , Force Current	---	---	80	A
Pulsed Source Current ^{2,6}	I _{SM}		---	---	320	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V , I _S =20A , T _J =25°C	---	---	1	V

Notes

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=75A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.Guaranteed by design, not subject to production testing.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

N- Channel Typical Characteristics

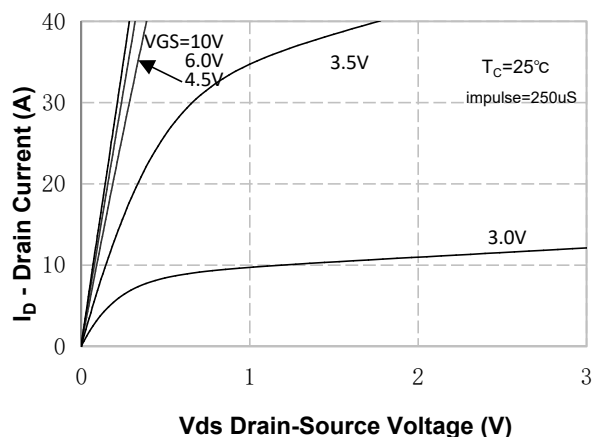


Figure 1. On-Region Characteristics

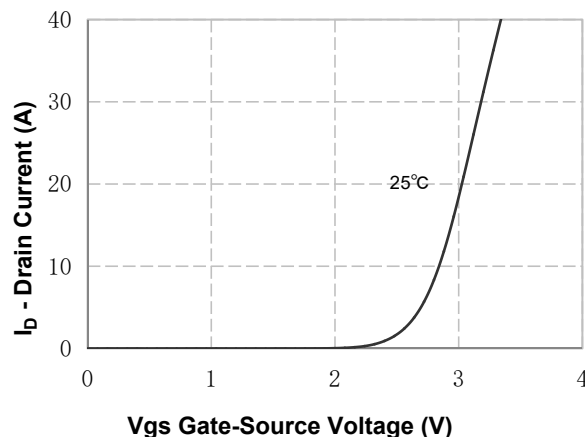


Figure 2. Transfer Characteristics

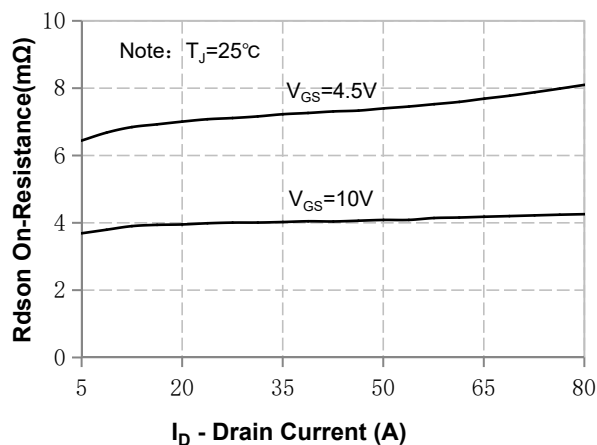


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

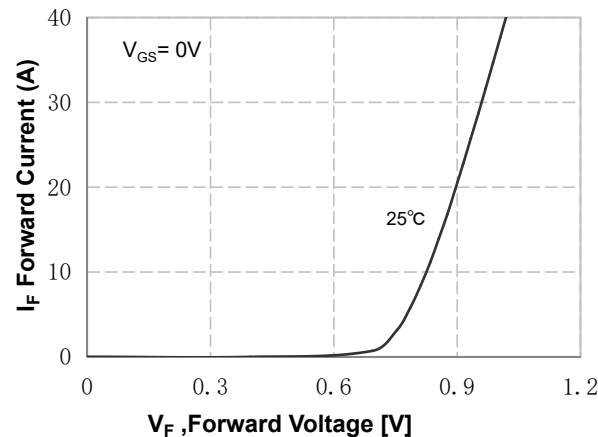


Figure 4. Body Diode Forward Voltage Variation vs Source Current

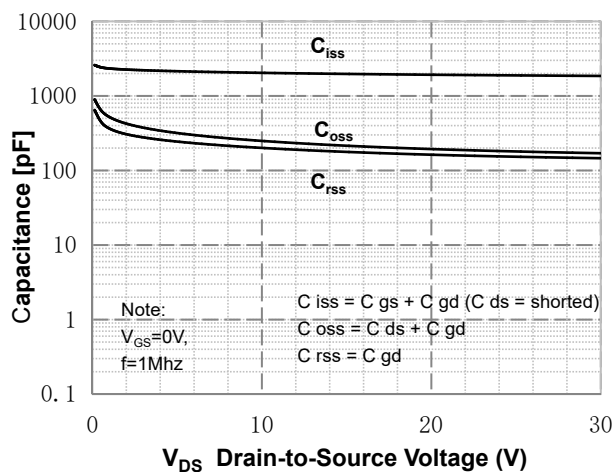


Figure 5. Capacitance Characteristics

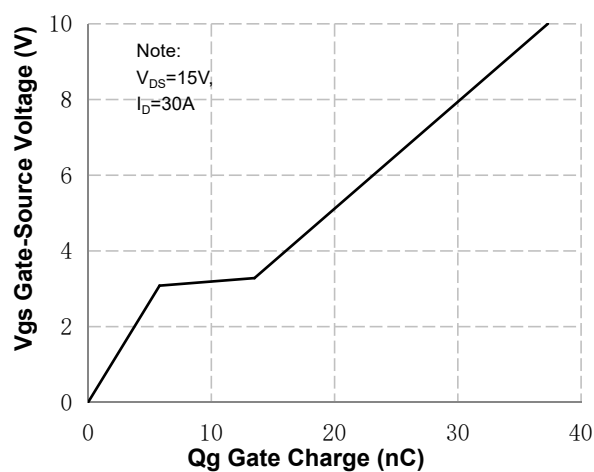


Figure 6. Gate Charge Characteristics

Typical Performance Characteristics

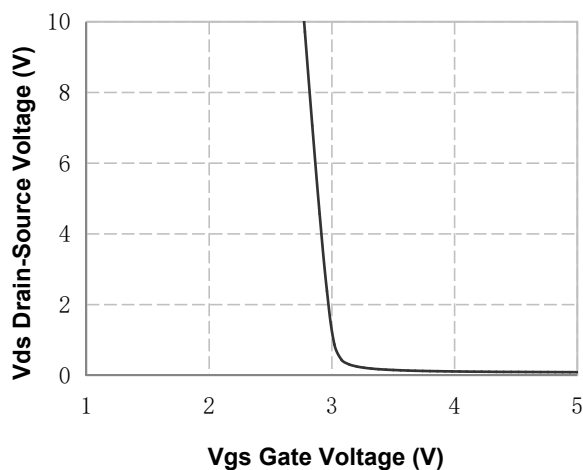


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

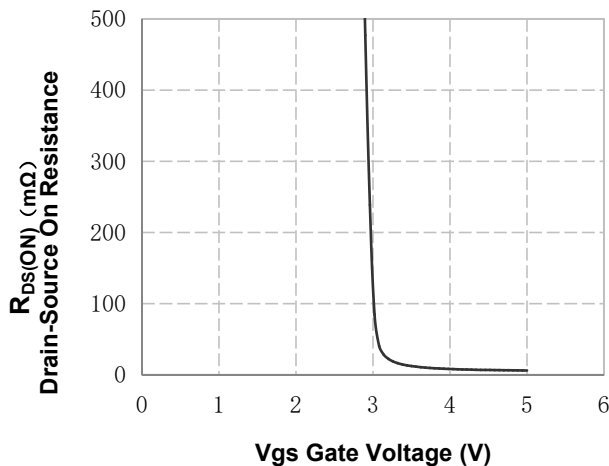


Figure 8. On-Resistance vs Gate Voltage

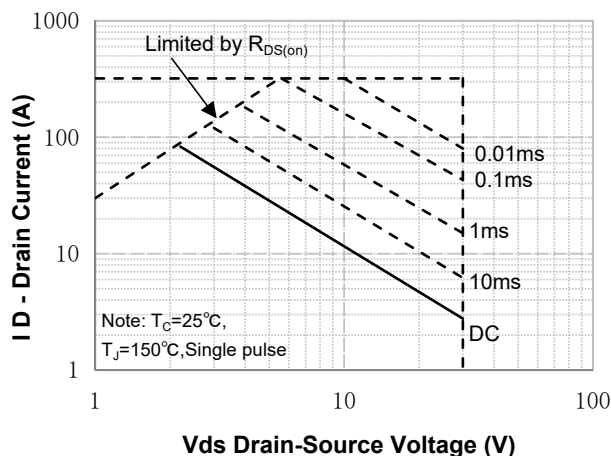


Figure 9. Maximum Safe Operating Area

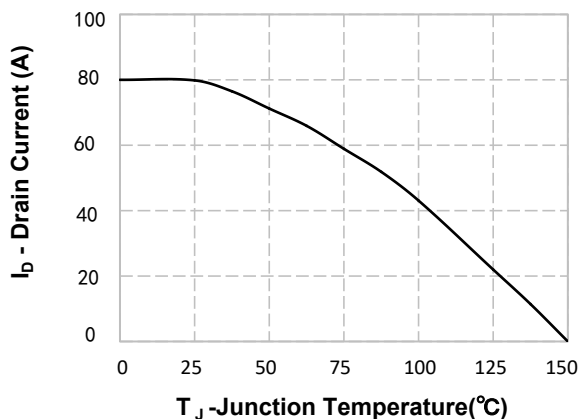


Figure 10. Maximum Continuous Drain Current vs Temperature

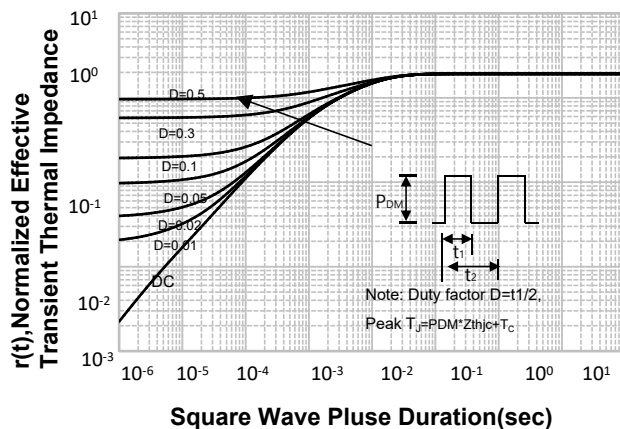
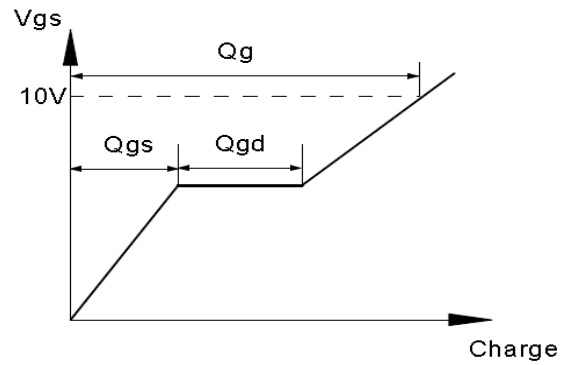
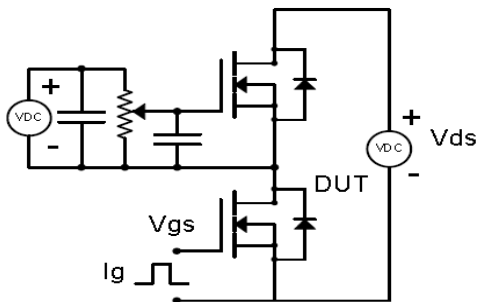


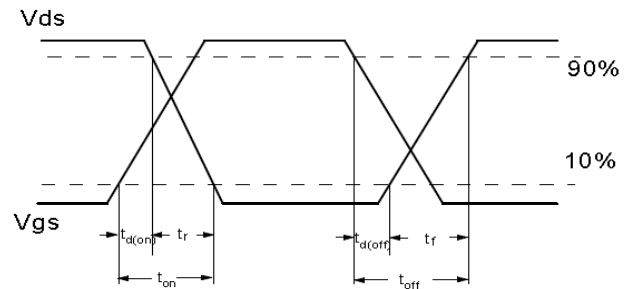
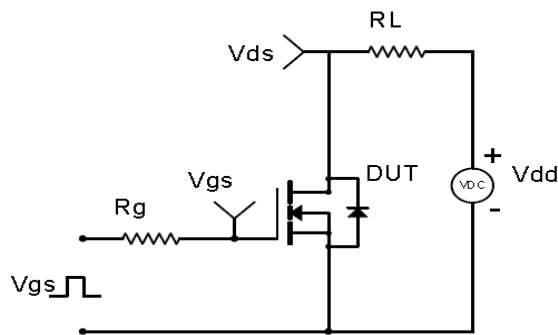
Figure 11. Transient Thermal Response Curve

Test Circuit & Waveform

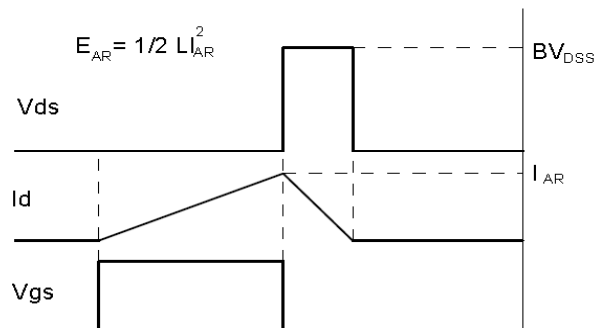
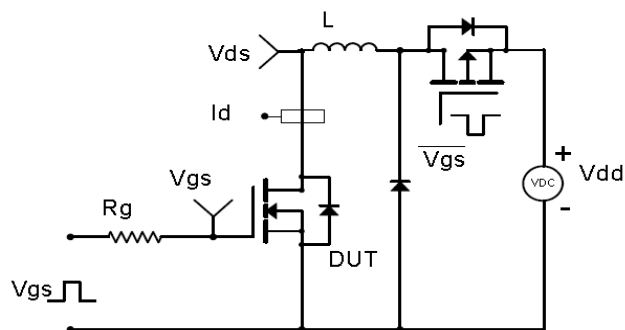
Gate Charge Test Circuit & Waveform



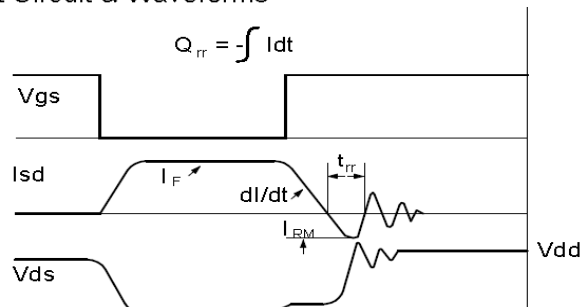
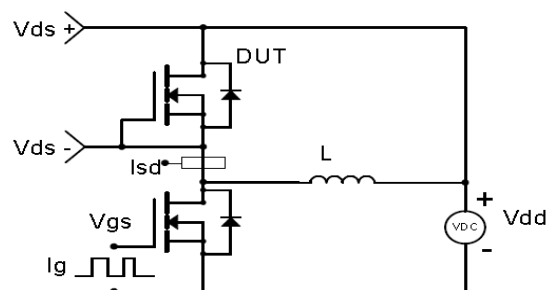
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

Important Notice

The information given in this document shall be for illustrative purposes only and shall in no event be regarded as a guarantee of conditions or characteristics. Gostone reserves the right to change any information herein. With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Gostone or its affiliates hereby make no representation or warranty of any kind, expressed or implied, as to any information provided hereunder, including without limitation as to the accuracy, completeness or non-infringement of intellectual property rights of any third party, and they assume no liability for the consequences of use of such information. In addition, any information given in this document is subject to customer's compliance with its obligations stated herein and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Gostone in customer's applications. The information contained herein is exclusively intended for technically trained staff. No license is granted by implication under any patent right, copyright, mask work right, or other intellectual property right. It is customer's sole responsibility to evaluate the suitability of the product for the intended application and the completeness of the product information given herein with respect to such application. In no event shall Gostone or its affiliates be liable to any party for any direct, indirect, special, punitive, incidental or consequential damages of any nature whatsoever, including but not limited to loss of profits and loss of goodwill, whether or not such damages are based on tort or negligence, warranty, breach of contract or any other legal theory. In addition, any recipient of this document and the relevant products samples may not alter, decompile, disassemble, reverse engineer, or otherwise modify any information/samples received hereunder. Any intellectual property rights arising from the reverse engineering of Gostone's products shall belong to Gostone.